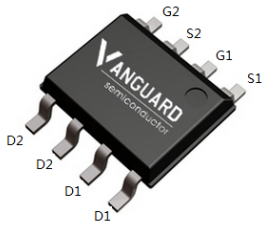
Features

- Dual P-Channel，-5V Logic Level Control
- Enhancement mode
- Very low on-resistance $R_{DS(on)}$ @ V_{GS}=-4.5 V
- Fast Switching
- High Effective
- Pb-free lead plating; RoHS compliant; Hg-Free

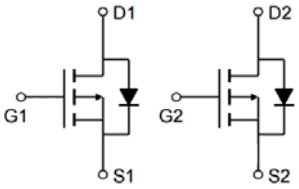
V_{DS}	-60	V
$R_{DS(on),TYP}$@ V_{GS}=-10 V	130	mΩ
$R_{DS(on),TYP}$@ V_{GS}=-4.5 V	160	mΩ
I_D	-3.4	A

SOP8



Pb-Free RoHS HF Halogen-Free

Part ID	Package Type	Marking	Tape and reel information
VSO200P06MD	SOP8	200P06MD	3000pcs/reel



Maximum ratings, at T_j=25 °C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		-60	V
I_S	Diode continuous forward current	T_A=25°C	-2.3	A
I_D	Continuous drain current@V_{GS}=10V	T_A=25°C	-3.4	A
		T_A=100°C	-2.1	A
I_{DM}	Pulse drain current tested ②	T_A=25°C	-13.6	A
P_D	Power dissipation for Dual Operation	T_A=25°C	3	W
V_{GS}	Gate-Source voltage		±20	V
T_{STG}	Storage temperature range		-55 to 150	°C
T_J	Maximum Junction Temperature①		150	°C

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	28	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	40	°C/W

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=-250μA	-60	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current(Tc=25℃)	V_{DS}=-60V,V_{GS}=0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(Tc=125℃)	V_{DS}=-60V,V_{GS}=0V	--	--	-100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=-250μA	-1.0	-2.0	-3.0	V
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=-10V, I_D=-2.5A	--	130	180	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=-4.5V, I_D=-1.5A	--	160	200	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=-30V,V_{GS}=0V, f=1MHz	--	500	--	pF
C_{oss}	Output Capacitance		--	30	--	pF
C_{rss}	Reverse Transfer Capacitance		--	20	--	pF
Q_g	Total Gate Charge	V_{DS}=-30V,I_D=-2A, V_{GS}=-10V	--	12	--	nC
Q_{gs}	Gate-Source Charge		--	1.8	--	nC
Q_{gd}	Gate-Drain Charge		--	4.2	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=-30V, I_D=-2A, R_G=6.8Ω, V_{GS}=-10V	--	8	--	nS
t_r	Turn-on Rise Time		--	10	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	22	--	nS
t_f	Turn-Off Fall Time		--	11	--	nS
Source- Drain Diode Characteristics@ T_J = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=-2.5A,V_{GS}=0V	--	-0.86	-1.3	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=-2A, V_{GS}=0V di/dt=-100A/μs	--	16.5	--	nS
Q_{rr}	Reverse Recovery Charge		--	8.8	--	nC

NOTE:

① Repetitive rating; pulse width limited by max. junction temperature.

②Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

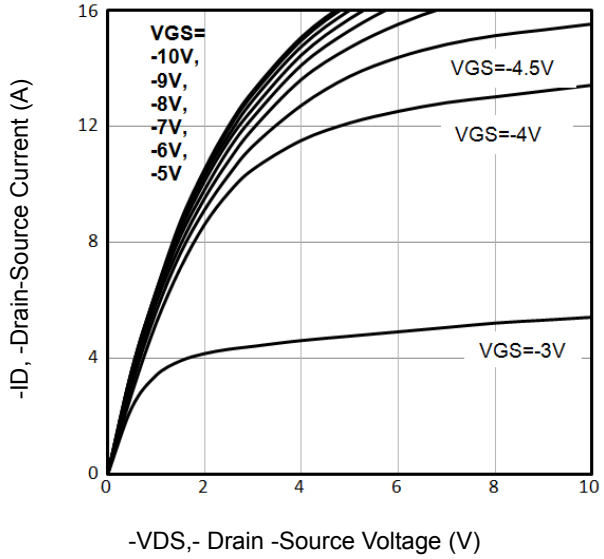


Fig1. Typical Output Characteristics

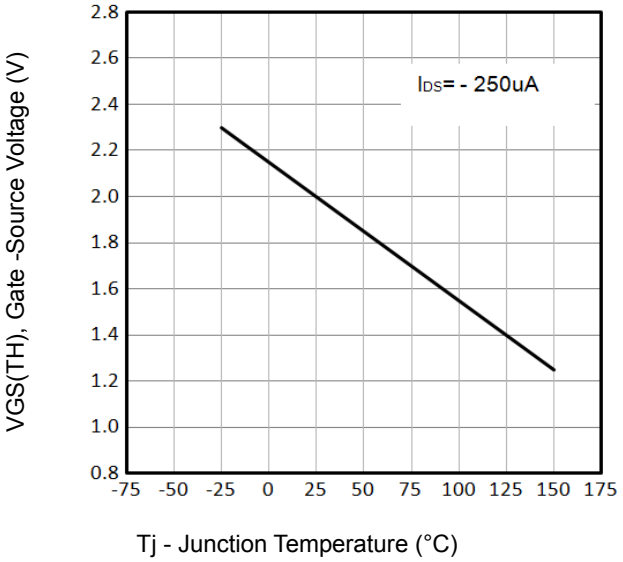


Fig2. $V_{GS(TH)}$ Gate -Source Voltage Vs.Tj

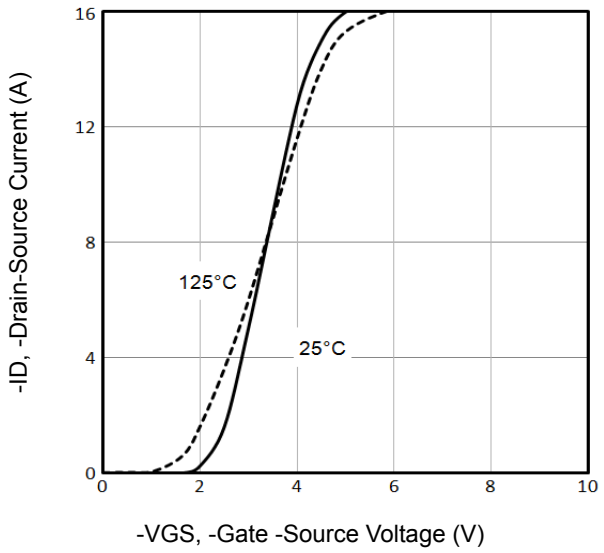


Fig3. Typical Transfer Characteristics

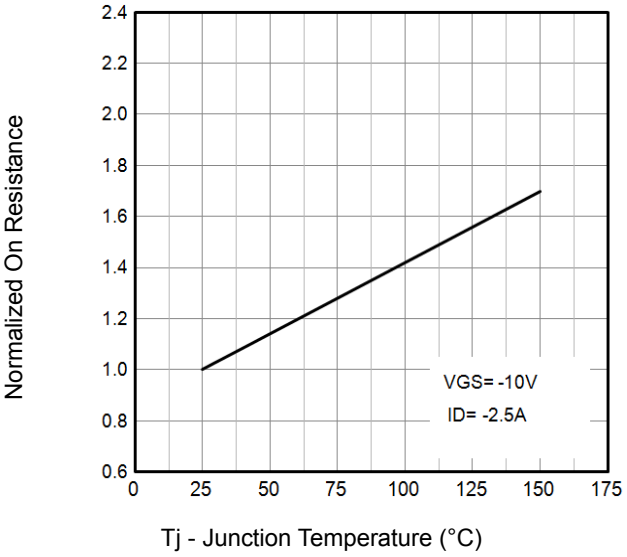


Fig4. Normalized On-Resistance Vs. Tj

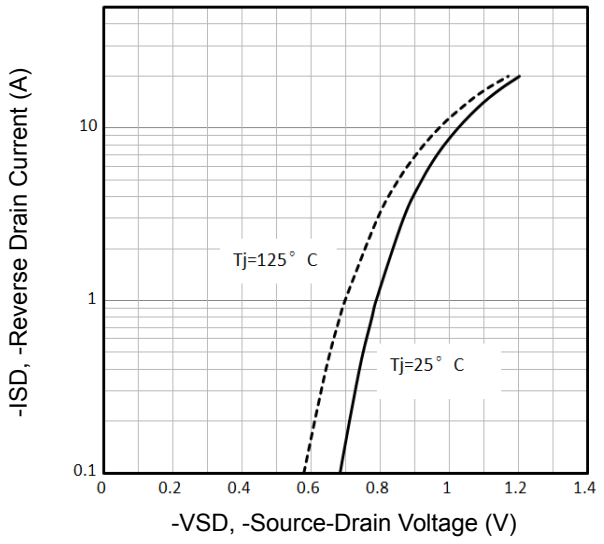


Fig5. Typical Source-Drain Diode Forward Voltage

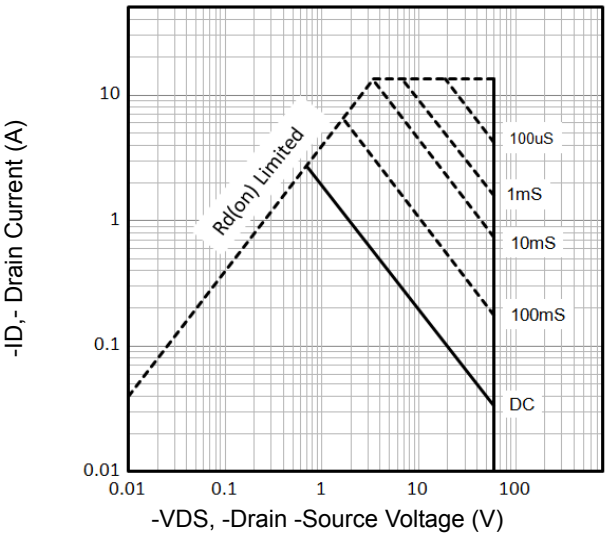


Fig6. Maximum Safe Operating Area

Typical Characteristics

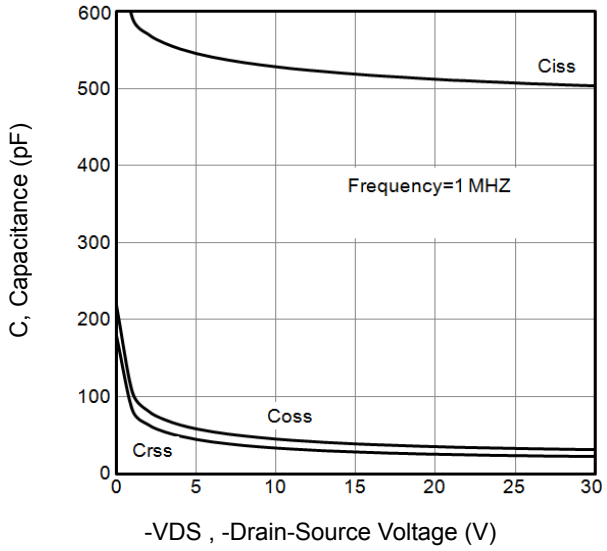


Fig7. Typical Capacitance Vs.Drain-Source Voltage

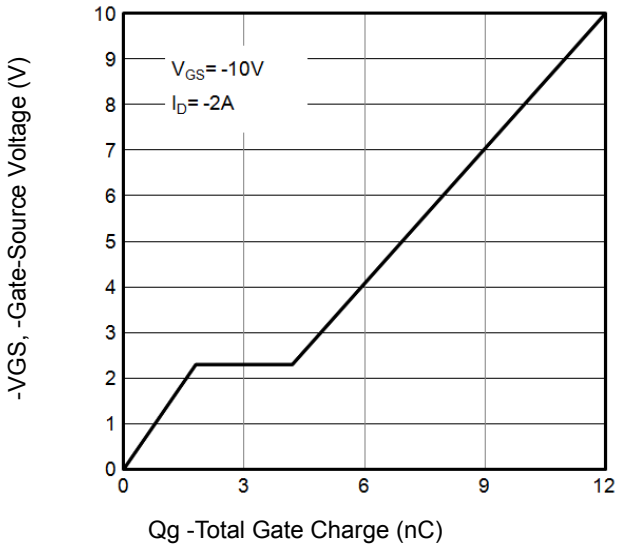


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

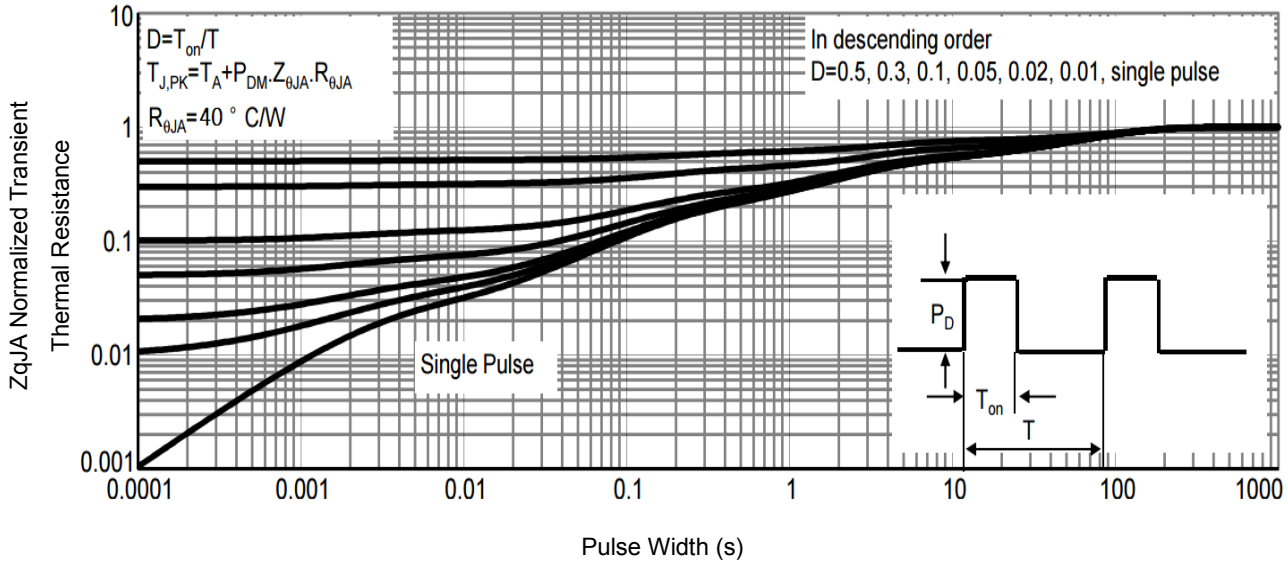


Fig9. Normalized Maximum Transient Thermal Impedance

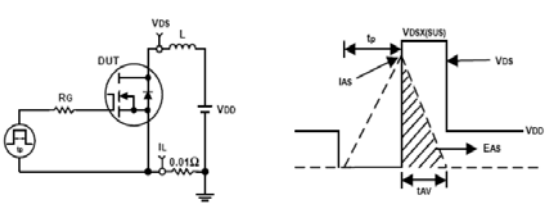


Fig10. Unclamped Inductive Test Circuit and Waveforms

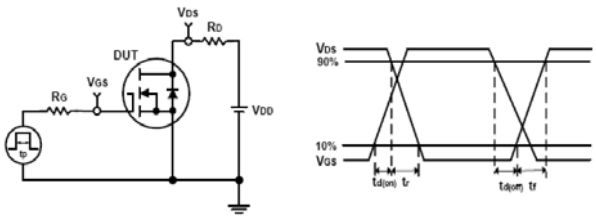
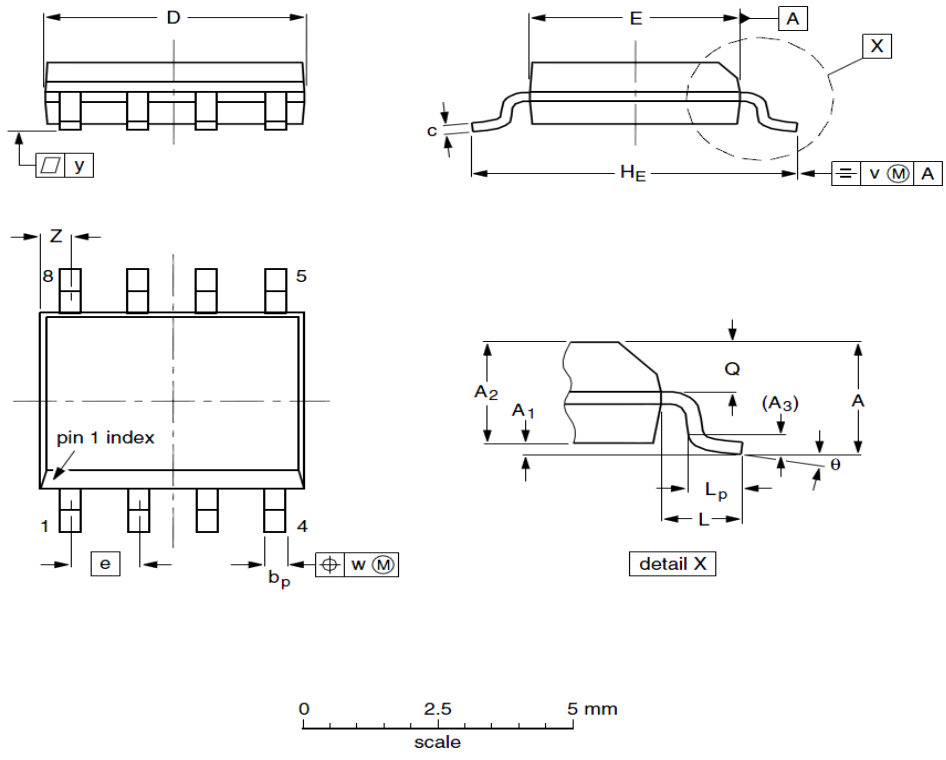


Fig11. Switching Time Test Circuit and waveforms

SOP8 Package Outline



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	--	1.75	--	**A_1**	0.10	0.18	0.25
A_2	1.25	1.35	1.45	**A_3**	--	0.25	--
b_p	0.36	0.42	0.49	**c**	0.19	0.22	0.25
D	4.80	4.92	5.00	**E**	3.80	3.90	4.00
e	--	1.27	--	**H_E**	5.80	5.98	6.20
L	--	1.05	--	**L_p**	0.40	0.68	1.00
Q	0.60	0.65	0.70	**v**	--	0.25	--
w	--	0.25	--	**y**	--	0.10	--
Z	0.30	0.50	0.70	**θ**	0°		8°

Customer Service

Sales and Service:

sales@vgsemi.com

Vanguard Semiconductor CO., LTD

TEL: (86-755) -26902410

FAX: (86-755) -26907027

WEB: **www.vgsemi.com**